



PATENTS

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE****Applicants:** Haruo Sunakawa, et al.**Examiner:** S. Mulpuri**Serial No.:** 09/821,411**Art Unit:** 2812**Filed:** March 29, 2001**Docket:** 14463**For:** METHOD OF MANUFACTURING A  
NITROGEN-BASED SEMICONDUCTOR  
SUBSTRATE AND A SEMICONDUCTOR  
ELEMENT BY USING THE SAME**Dated:** September 23, 2002Assistant Commissioner for Patents  
Washington, D.C. 20231**RESPONSE**

Sir:

In response to the Office Action dated May 22, 2002, applicants submit the following Amendment for entry in the above-identified application.

**IN THE SPECIFICATION:**

Please replace the paragraph beginning on Page 12, line 27 with the following:

As shown in Fig. 2B, a SiO<sub>2</sub> film 16 is deposited to a thickness of 200nm on the surface of the GaN film 15 and a protection film 17 is formed on the SiO<sub>2</sub> film 16. The illustrated protection film 17 is composed of a titanium (Ti) film of 50nm thick and a gold (Au) film of 0.4μm thick. After deposition of the protection film 17, a heat treatment is carried out at a temperature of 450°C for ten minutes within a hydrogen atmosphere.

**CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner of Patents and Trademarks, Washington, D.C. 20231 on September 23, 2002.

**Dated:** September 23, 2002  
Michelle Mustafa